



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Features

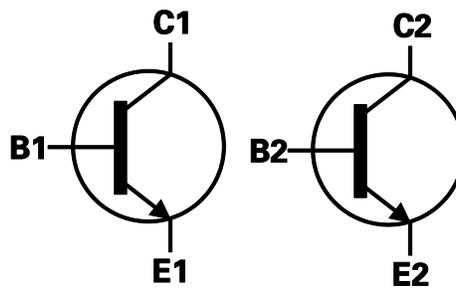
- Ultra-Small Surface-Mount Package
- Epitaxial Planar Die Construction
- Ideal for Low-Power Amplification and Switching

## Mechanical Data

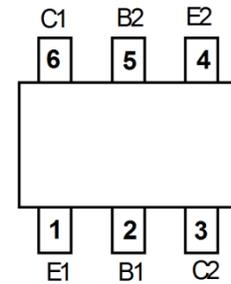
- Package: SOT363
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 Ⓔ③
- Weight: 0.006 grams (Approximate)



Top View



Device Symbol



Top View  
Pin-Out

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	600	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes: 5. For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.  
 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

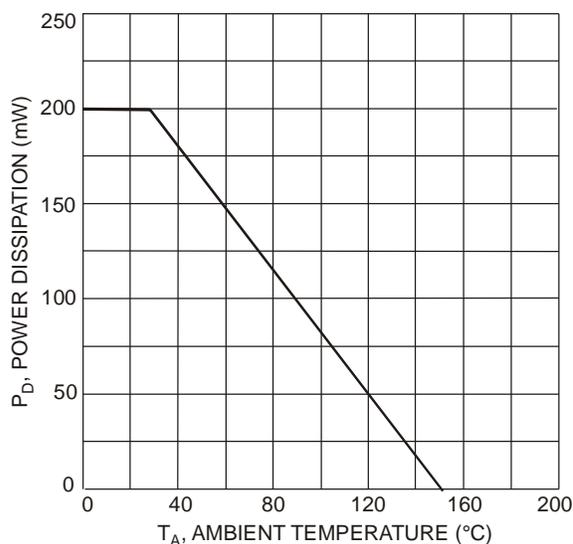


Fig. 1 Power Derating Curve

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	60	—	—	V	I <sub>C</sub> = -10μA, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage (Note 7)	BV <sub>CEO</sub>	40	—	—	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6.0	—	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	—	100	nA	V <sub>CE</sub> = 35V, V <sub>EB(off)</sub> = 0.4V
Base Cutoff Current	I <sub>BL</sub>	—	—	100	nA	V <sub>CE</sub> = 35V, V <sub>EB(off)</sub> = 0.4V
<b>ON CHARACTERISTICS (Note 7)</b>						
DC Current Gain	h <sub>FE</sub>	20	—	—	—	I <sub>C</sub> = 100μA, V <sub>CE</sub> = 1.0V
		40	—	—		I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 1.0V
		80	—	—		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1.0V
		100	—	300		I <sub>C</sub> = 150mA, V <sub>CE</sub> = 1.0V
		40	—	—		I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2.0V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	—	0.4 0.75	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.75 —	—	0.95 1.2	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	C <sub>obo</sub>	—	—	6.5	pF	V <sub>CB</sub> = 5V, f = 1MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	—	30	pF	V <sub>EB</sub> = 0.5V, f = 1MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>ie</sub>	1.0	—	15	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA f = 1kHz
Voltage Feedback Ratio	h <sub>re</sub>	0.1	—	8.0	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>fe</sub>	40	—	500	—	
Output Admittance	h <sub>oe</sub>	1.0	—	30	μS	
Current Gain Bandwidth Product	f <sub>T</sub>	250	—	—	MHz	
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Delay Time	t <sub>d</sub>	—	—	15	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA
Rise Time	t <sub>r</sub>	—	—	20	ns	V <sub>BE(off)</sub> = 2.0V, I <sub>B1</sub> = 15mA
Storage Time	t <sub>s</sub>	—	—	225	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA
Fall Time	t <sub>f</sub>	—	—	30	ns	I <sub>B1</sub> = -I <sub>B2</sub> = 15mA

Note: 7. Short duration pulse test used to minimize self-heating effect.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

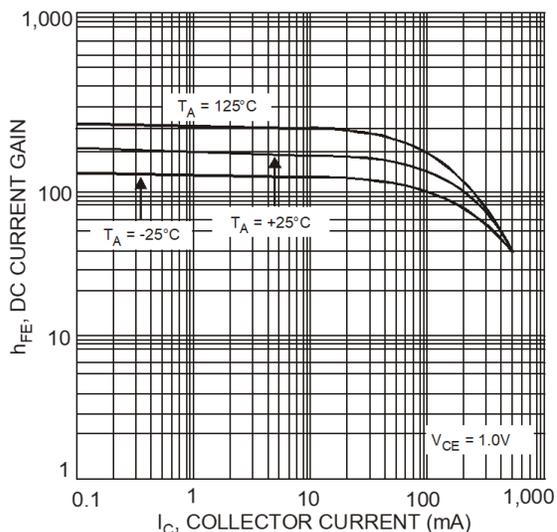


Fig. 2 Typical DC Current Gain vs. Collector Current

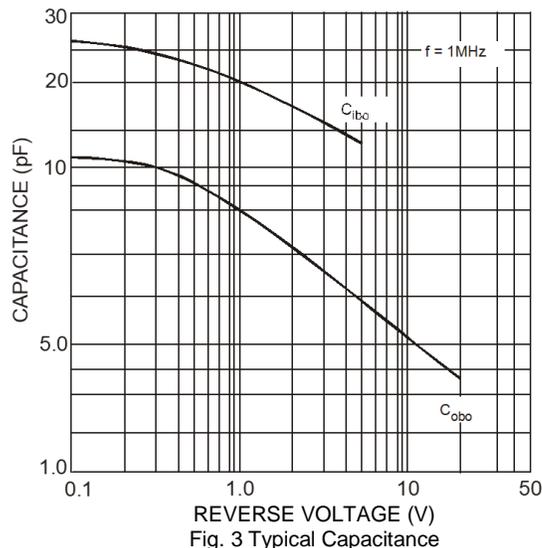


Fig. 3 Typical Capacitance

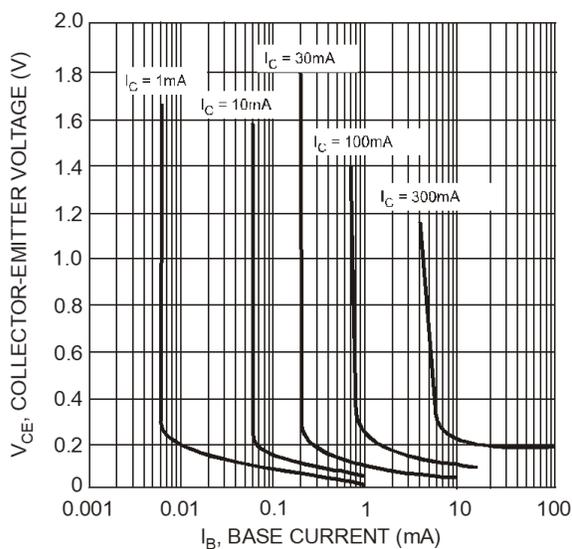


Fig. 4 Typical Collector Saturation Region

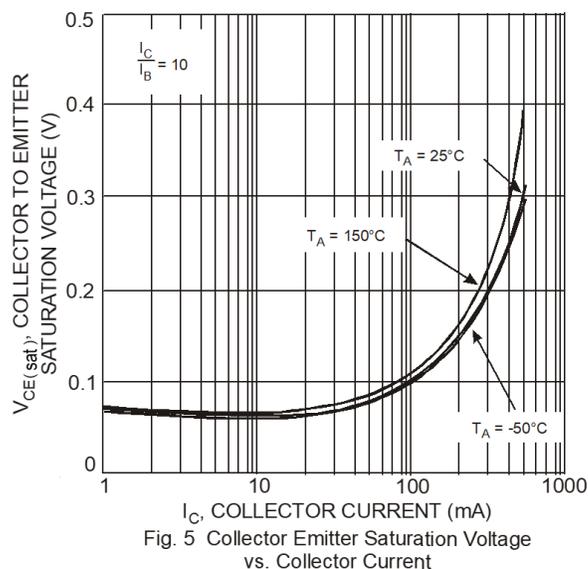


Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

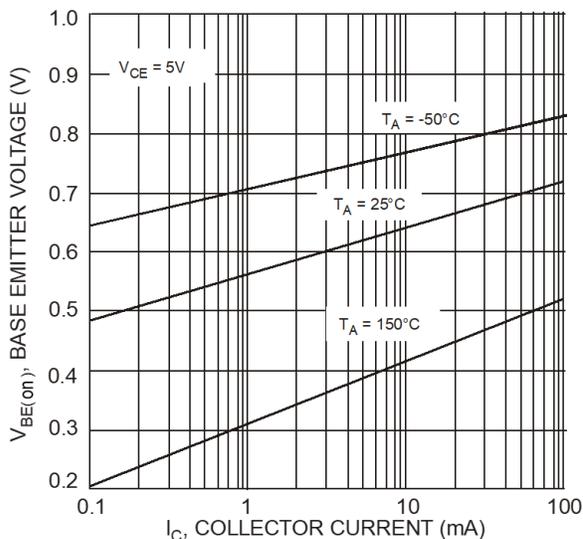


Fig. 6 Base Emitter Voltage vs. Collector Current

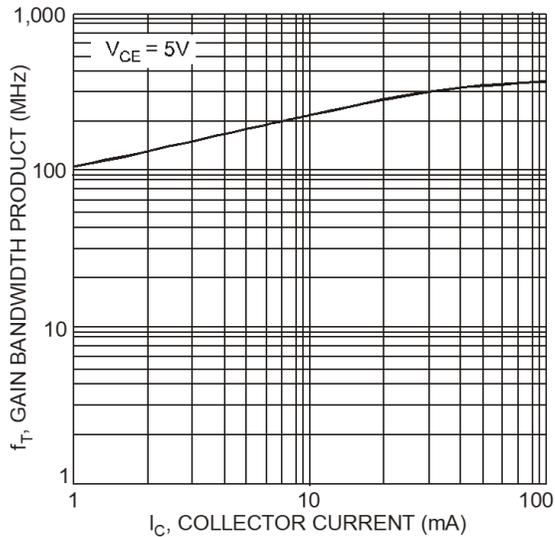
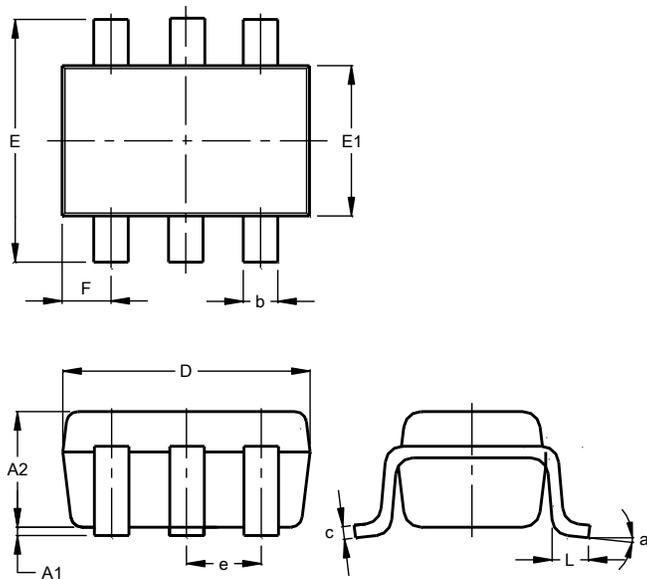


Fig. 7 Gain Bandwidth Product vs. Collector Current

**Package Outline Dimensions**

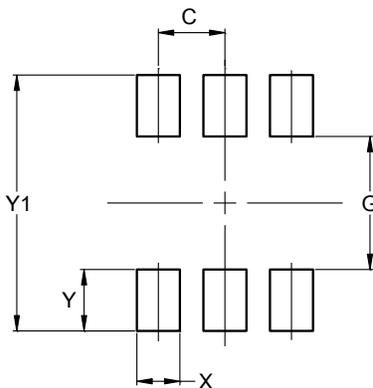
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500